Fudan Energy Storage Device

Recently a team at Fudan University claimed to have developed a picosecond-level Flash memory device (called "PoX") that has an access time of a mere 400 picoseconds.

An integrated device for both photoelectric conversion and energy storage based on free-standing and aligned carbon nanotube film" J. Mater. Chem. A., 2013, 1, 954-958.

Researchers at Fudan University have made a significant advancement in integrated circuit technology. The team led by Zhou Peng and Liu Chunsen has developed "PoX," a picosecond ...

Researchers at Fudan University in Shanghai have unveiled a flash memory device that breaks speed records once thought unreachable. Dubbed "PoX," the device can program data in just ...

With its unprecedented picosecond-level flash memory innovation, the PoX device is poised to redefine our approach to analytics, hastening the end of speed limits that once constrained ...

Described by Zhou Peng, a leading researcher from the university"s State Key Laboratory of Integrated Chips and Systems, as operating "1 billion times in the blink of an eye," this device ...

Setting a new benchmark for Flash memory performance, a team of researchers at Fudan University in Shanghai has developed a super-fast, picosecond-level non-volatile memory device.

Researchers from Shanghai-based Fudan University have developed a picosecond-level flash memory device with an unprecedented program speed of 400 picoseconds, equivalent to ...

A research team at Fudan University has built the fastest semiconductor storage device ever reported, a non-volatile flash memory dubbed "PoX" that programs a single bit in 400 ...

Peng Huisheng"s team at Fudan University first proposed it in 2013 and realized the first fiber lithium-ion battery in the world . The battery is a flexible one-dimensional fiber that can be woven into various ...

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